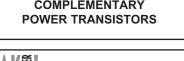
# CJD200 NPN CJD210 PNP

# SURFACE MOUNT SILICON COMPLEMENTARY







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# DESCRIPTION:

The CENTRAL SEMICONDUCTOR CJD200 and CJD210 are complementary silicon power transistors manufactured in a surface mount package designed for high current amplifier applications.

MARKING: FULL PART NUMBER

| MAXIMUM R   | RATINGS: (T <sub>C</sub> =25°C unless otherwise          | e noted)                          |             |       |
|---|--|-----------------------------------|-------------|-------|
|   |  | SYMBOL                            |             | UNITS |
| Collector-Bas   | se Voltage   | V <sub>CBO</sub>                  | 40          | V     |
| Collector-Emitter Voltage                                     |  | $V_{CEO}$                         | 25          | V     |
| Emitter-Base  | Voltage  | $V_{EBO}$                         | 8.0         | V     |
| Continuous Collector Current                                  |  | I <sub>C</sub>                    | 5.0         | Α     |
| Peak Collector Current Continuous Base Current                |  | I <sub>CM</sub>                   | 10          | Α     |
| Continuous E  | Base Current   | Ι <sub>Β</sub>                    | 1.0         | Α     |
| Power Dissip  | pation   | $P_{D}$                           | 12.5        | W     |
| Power Dissipation (T <sub>A</sub> =25°C)                      |  | $P_{D}$                           | 1.4         | W     |
| Operating and Storage Junction Temperature Thermal Resistance |  | T <sub>J</sub> , T <sub>stg</sub> | -65 to +150 | °C    |
|   |  | $\Theta$ JC                       | 10          | °C/W  |
| Thermal Resistance  |  | $\Theta_{\sf JA}$                 | 89.3        | °C/W  |
| FI FCTRICA  | L CHARACTERISTICS: (T <sub>C</sub> =25°C ui              | nless otherwise n                 | oted)       |       |
| SYMBOL  | TEST CONDITIONS  | MIN                               | MAX         | UNITS |
| I <sub>CBO</sub>  | V <sub>CB</sub> =40V                                     |                                   | 100         | nA    |
| I <sub>CBO</sub>  | V <sub>CB</sub> =40V, T <sub>C</sub> =125°C              |                                   | 100         | μΑ    |
| I <sub>EBO</sub>  | V <sub>EB</sub> =8.0V                                    |                                   | 100         | nA    |
| BVCEO   | I <sub>C</sub> =10mA                                     | 25                                |             | V     |
| V <sub>CE(SAT)</sub>  | I <sub>C</sub> =500mA, I <sub>B</sub> =50mA              |                                   | 0.3         | V     |
| V <sub>CE(SAT)</sub>  | I <sub>C</sub> =2.0A, I <sub>B</sub> =200mA              |                                   | 0.75        | V     |
| V <sub>CE(SAT)</sub>  | I <sub>C</sub> =5.0A, I <sub>B</sub> =1.0A               |                                   | 1.8         | V     |
| V <sub>BE(SAT)</sub>  | I <sub>C</sub> =5.0A, I <sub>B</sub> =1.0A               |                                   | 2.5         | V     |
| V <sub>BE(ON)</sub>   | V <sub>CF</sub> =1.0V, I <sub>C</sub> =2.0A              |                                   | 1.6         | V     |
| h <sub>FE</sub>   | V <sub>CE</sub> =1.0V, I <sub>C</sub> =500mA             | 70                                |             |       |
| h <sub>FE</sub>   | $V_{CE}$ =1.0V, $I_{C}$ =2.0A                            | 45                                | 180         |       |
| h <sub>FE</sub>   | $V_{CE}$ =2.0V, $I_{C}$ =5.0A                            | 10                                |             |       |
| f <sub>T</sub>  | V <sub>CE</sub> =10V, I <sub>C</sub> =100mA, f=10MHz     | 65                                |             | MHz   |
| C <sub>ob</sub>   | V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=0.1MHz (CJD20 | 0)                                | 80          | pF    |
| C <sub>ob</sub>   | $V_{CB}$ =10V, $I_E$ =0, f=0.1MHz (CJD21                 | 0)                                | 120         | pF    |

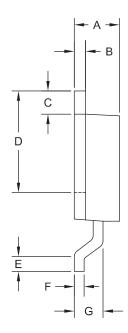
R3 (21-January 2013)

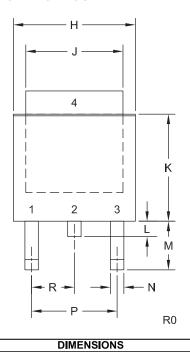
# CJD200 NPN CJD210 PNP

# **SURFACE MOUNT SILICON COMPLEMENTARY POWER TRANSISTORS**



#### **DPAK CASE - MECHANICAL OUTLINE**





# LEAD CODE:

- 1) Base
- 2) Collector
- 3) Emitter 4) Collector

#### MARKING: **FULL PART NUMBER**

| DIVILIAZIONS   |        |       |             |      |  |  |  |  |
|----------------|--------|-------|-------------|------|--|--|--|--|
|                | INCHES |       | MILLIMETERS |      |  |  |  |  |
| SYMBOL         | MIN    | MAX   | MIN         | MAX  |  |  |  |  |
| Α              | 0.083  | 0.108 | 2.10        | 2.75 |  |  |  |  |
| В              | 0.016  | 0.032 | 0.40        | 0.81 |  |  |  |  |
| С              | 0.035  | 0.063 | 0.89        | 1.60 |  |  |  |  |
| D              | 0.203  | 0.228 | 5.15        | 5.79 |  |  |  |  |
| E              | 0.020  | -     | 0.51        | -    |  |  |  |  |
| F              | 0.018  | 0.024 | 0.45        | 0.60 |  |  |  |  |
| G              | 0.051  | 0.071 | 1.30        | 1.80 |  |  |  |  |
| Н              | 0.248  | 0.268 | 6.30        | 6.81 |  |  |  |  |
| J              | 0.197  | 0.217 | 5.00        | 5.50 |  |  |  |  |
| K              | 0.209  | 0.245 | 5.30        | 6.22 |  |  |  |  |
| L              | 0.025  | 0.040 | 0.64        | 1.02 |  |  |  |  |
| M              | 0.090  | 0.115 | 2.30        | 2.91 |  |  |  |  |
| N              | 0.012  | 0.045 | 0.30        | 1.14 |  |  |  |  |
| Р              | 0.180  |       | 4.60        |      |  |  |  |  |
| R              | 0.090  |       | 2.30        |      |  |  |  |  |
| DPAK (REV: R0) |        |       |             |      |  |  |  |  |

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